

Zhuo Deng

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7126036/publications.pdf>

Version: 2024-02-01

28
papers

470
citations

687363

13
h-index

713466

21
g-index

28
all docs

28
docs citations

28
times ranked

462
citing authors

#	ARTICLE	IF	CITATIONS
1	High-speed uni-traveling carrier photodiode for 2.5-4 μm wavelength application. <i>Optica</i> , 2019, 6, 884.	9.3	65
2	Inverted Si:PbS Colloidal Quantum Dot Heterojunction-Based Infrared Photodetector. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 15414-15421.	8.0	53
3	Demonstration of InAs/InGaAs/GaAs Quantum Dots-in-a-Well Mid-Wave Infrared Photodetectors Grown on Silicon Substrate. <i>Journal of Lightwave Technology</i> , 2018, 36, 2572-2581.	4.6	36
4	High-speed mid-wave infrared interband cascade photodetector at room temperature. <i>Optics Express</i> , 2020, 28, 36915.	3.4	28
5	High-Speed Mid-Infrared Interband Cascade Photodetector Based on InAs/GaAsSb Type-II Superlattice. <i>Journal of Lightwave Technology</i> , 2020, 38, 939-945.	4.6	26
6	Low frequency noise-dark current correlations in HgCdTe infrared photodetectors. <i>Optics Express</i> , 2020, 28, 23660.	3.4	26
7	Recent Advances in High Speed Photodetectors for eSWIR/MWIR/LWIR Applications. <i>Photonics</i> , 2021, 8, 14.	2.0	25
8	Sub-monolayer quantum dot quantum cascade mid-infrared photodetector. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	24
9	Midwave Infrared Quantum Dot Quantum Cascade Photodetector Monolithically Grown on Silicon Substrate. <i>Journal of Lightwave Technology</i> , 2018, 36, 4033-4038.	4.6	24
10	Dynamic model and bandwidth characterization of InGaAs/GaAsSb type-II quantum wells PIN photodiodes. <i>Optics Express</i> , 2018, 26, 35034.	3.4	21
11	InP-Based Near Infrared/Extended-Short Wave Infrared Dual-Band Photodetector. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 1003-1006.	2.5	19
12	Demonstration of Si based InAs/GaSb type-II superlattice p-i-n photodetector. <i>Infrared Physics and Technology</i> , 2019, 101, 133-137.	2.9	17
13	Direct growth of InAs/GaSb type II superlattice photodiodes on silicon substrates. <i>IET Optoelectronics</i> , 2018, 12, 2-4.	3.3	16
14	Mid-Wave Infrared InAs/GaSb Type-II Superlattice Photodetector With n-B-p Design Grown on GaAs Substrate. <i>IEEE Journal of Quantum Electronics</i> , 2019, 55, 1-5.	1.9	13
15	Low-Frequency Noise Spectroscopy Characterization of HgCdTe Infrared Detectors. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 547-551.	3.0	11
16	Demonstration of a Dual-Band InAs/GaSb Type-II Superlattice Infrared Detector Based on a Single Heterojunction Diode. <i>IEEE Journal of Quantum Electronics</i> , 2020, 56, 1-6.	1.9	10
17	Long-Wave Infrared Sub-Monolayer Quantum dot Quantum Cascade Photodetector. <i>Journal of Lightwave Technology</i> , 2021, 39, 1489-1496.	4.6	8
18	Optical properties of beryllium-doped GaSb epilayers grown on GaAs substrate. <i>Infrared Physics and Technology</i> , 2018, 90, 115-121.	2.9	7

#	ARTICLE	IF	CITATIONS
19	Submonolayer quantum dot quantum cascade long-wave infrared photodetector grown on Ge substrate. Applied Physics Letters, 2021, 118, .	3.3	7
20	Characteristics of thin InAlAs digital alloy avalanche photodiodes. Optics Letters, 2021, 46, 3841.	3.3	7
21	Demonstration of MOCVD-Grown Long-Wavelength Infrared InAs/GaSb Superlattice Focal Plane Array. IEEE Access, 2021, 9, 60689-60694.	4.2	6
22	Deep levels analysis in wavelength extended InGaAsBi photodetector. Semiconductor Science and Technology, 2019, 34, 095018.	2.0	5
23	High-Speed 850 nm Photodetector for Zero-Bias Operation. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-7.	2.9	5
24	Defect characterization of AlInAsSb digital alloy avalanche photodetectors with low frequency noise spectroscopy. Optics Express, 2020, 28, 11682.	3.4	5
25	Temperature-Dependent Characteristics of HgCdTe Mid-Wave Infrared E-Avalanche Photodiode. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-9.	2.9	4
26	InP-Based Extended-Short Wave Infrared Heterojunction Phototransistor. Journal of Lightwave Technology, 2021, 39, 4814-4819.	4.6	2
27	Mid-wave InAs/GaSb Superlattice PiBN Infrared Photodetector Grown on GaAs Substrate. , 2018, , .		0
28	Dark Current Analysis of Mid-Wave Quantum Dots-in-a-Well Photodetectors Monolithically Grown on Silicon Substrate. , 2018, , .		0